



JB748

15kV, 10mA, 50nS
High Voltage Silicon Diode



Features

- Fast Reverse Recovery Time for High Efficiency
- Molded Plastic Body, ANSI/UL94 V-0 Rated Material

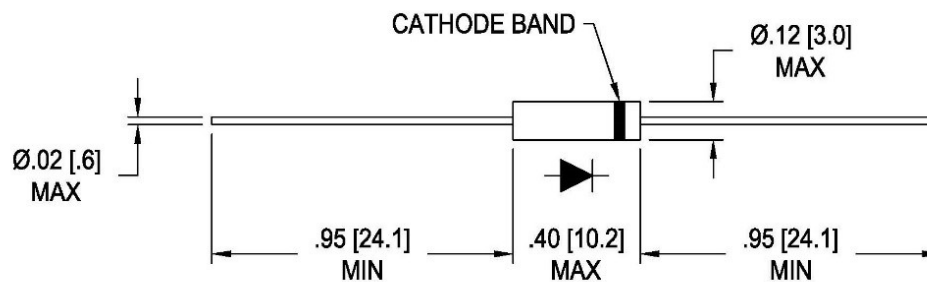
Specifications

Part Number	Values						
	V_{RRM} Maximum Repetitive Reverse Voltage (V)	I_{FAVM} Maximum Average Forward Current (mA) At T _A = 55°C	V_F Maximum Forward Voltage Drop (V) At I _F = 5mA	I_R Maximum Leakage Current (μA) At V _{RRM}	I_{FSM} Maximum Surge Current (A) At 8.3 ms, Single Half Sine	C_J Typical Junction Capacitance (pF) At V _R = 0VDC, f = 1MHz	T_{RR} Maximum Reverse Recovery Time (nS) I _F = 10mA; I _R = -25mA; I _{RR} = -5mA
JB748	15000	10	25	0.2	3	0.26	50

Note: Specifications are measured with a 25°C ambient temperature unless stated otherwise.

Temperature		
T_{STG}	Storage Temperature	-40 to 150°C
T_{OP}	Operating Temperature	-40 to 125°C
T_{JMAX}	Maximum Junction Temperature	125°C

Case Outline and Dimensions



Dimensions in inches [mm]



Note: Specifications subject to change without notice. Photo is representation only.